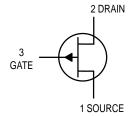
JFET Amplifiers

P-Channel — Depletion



2N5460 thru 2N5462

MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Drain-Gate Voltage	V _{DG}	40	Vdc	
Reverse Gate – Source Voltage	VGSR	40	Vdc	
Forward Gate Current	IG(f)	10	mAdc	
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	350 2.8	mW mW/°C	
Junction Temperature Range	TJ	-65 to +135	°C	
Storage Channel Temperature Range	T _{stg}	-65 to +150	°C	



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit		
OFF CHARACTERISTICS								
Gate-Source Breakdown Voltage (I _G = 10 μAdc, V _{DS} = 0)	2N5460, 2N5461, 2N5462	V(BR)GSS	40	_	_	Vdc		
Gate Reverse Current (V _{GS} = 20 Vdc, V _{DS} = 0) (V _{GS} = 30 Vdc, V _{DS} = 0)	2N5460, 2N5461, 2N5462	IGSS	_	_	5.0	nAdc		
(V _{GS} = 20 Vdc, V _{DS} = 0, T _A = 100°C) (V _{GS} = 30 Vdc, V _{DS} = 0, T _A = 100°C)	2N5460, 2N5461, 2N5462		_	_	1.0	μAdc		
Gate – Source Cutoff Voltage (V _{DS} = 15 Vdc, I _D = 1.0 μAdc)	2N5460 2N5461 2N5462	VGS(off)	0.75 1.0 1.8	_ _ _	6.0 7.5 9.0	Vdc		
$\label{eq:Gate-Source Voltage} \begin{split} &\text{Gate-Source Voltage} \\ &\text{(V}_{DS} = 15 \text{ Vdc, I}_{D} = 0.1 \text{ mAdc)} \\ &\text{(V}_{DS} = 15 \text{ Vdc, I}_{D} = 0.2 \text{ mAdc)} \\ &\text{(V}_{DS} = 15 \text{ Vdc, I}_{D} = 0.4 \text{ mAdc)} \end{split}$	2N5460 2N5461 2N5462	V _{GS}	0.5 0.8 1.5	_ _ _	4.0 4.5 6.0	Vdc		
ON CHARACTERISTICS								
Zero-Gate-Voltage Drain Current (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 kHz)	2N5460 2N5461 2N5462	I _{DSS}	-1.0 -2.0 -4.0	_ _ _	-5.0 -9.0 -16	mAdc		
SMALL-SIGNAL CHARACTERISTICS	3							
Forward Transfer Admittance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 kHz)	2N5460 2N5461 2N5462	y _{fs}	1000 1500 2000	_ 	4000 5000 6000	μmhos		
Output Admittance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 kHz)		y _{os}		_	75	μmhos		
Input Capacitance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 MHz)		C _{iss}	_	5.0	7.0	pF		
Reverse Transfer Capacitance (V _{DS} = 15 Vdc, V _{GS} = 0, f = 1.0 MHz)		C _{rss}	_	1.0	2.0	pF		
FUNCTIONAL CHARACTERISTICS								
Noise Figure $(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, R_G = 1.0 \text{ Megohm}, f = 100 \text{ Hz}, BW = 1.0 \text{ Hz})$		NF	_	1.0	2.5	dB		
Equivalent Short–Circuit Input Noise Voltage $(V_{DS} = 15 \text{ Vdc}, V_{GS} = 0, f = 100 \text{ Hz}, BW = 1.0 \text{ Hz})$		e _n	_	60	115	nV/√ Hz		

DRAIN CURRENT versus GATE SOURCE VOLTAGE

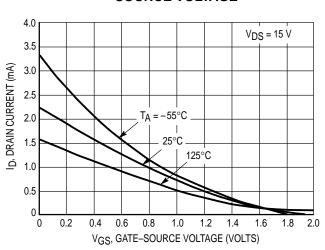


Figure 1. VGS(off) = 2.0 Volts

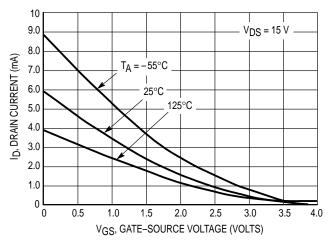


Figure 2. VGS(off) = 4.0 Volts

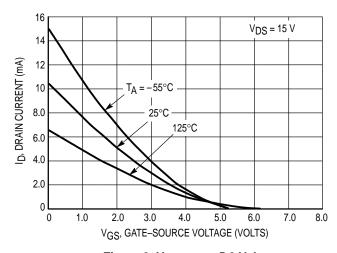


Figure 3. VGS(off) = 5.0 Volts

FORWARD TRANSFER ADMITTANCE versus DRAIN CURRENT

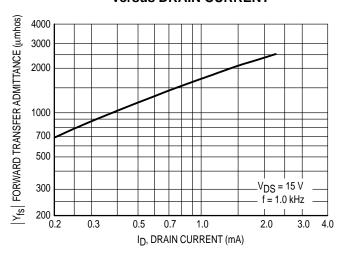


Figure 4. VGS(off) = 2.0 Volts

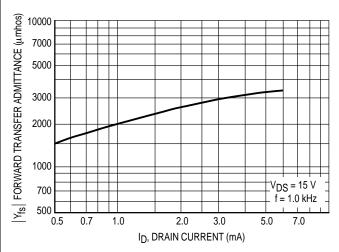


Figure 5. VGS(off) = 4.0 Volts

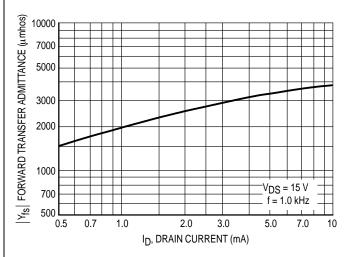


Figure 6. VGS(off) = 5.0 Volts

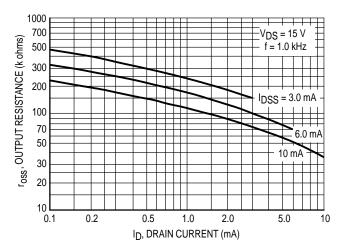


Figure 7. Output Resistance versus Drain Current

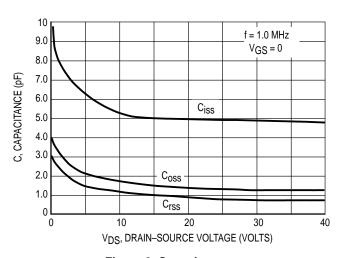


Figure 8. Capacitance versus Drain-Source Voltage

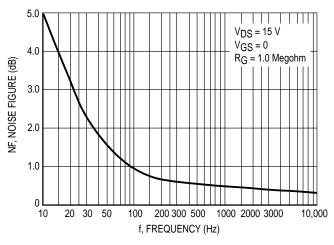


Figure 9. Noise Figure versus Frequency

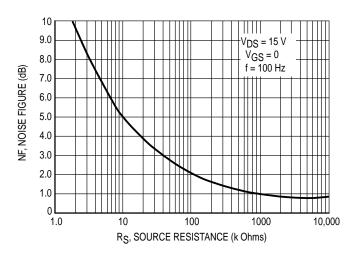
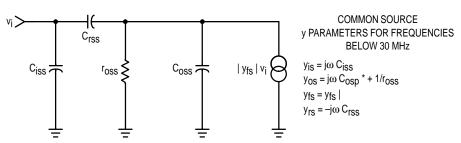


Figure 10. Noise Figure versus Source Resistance



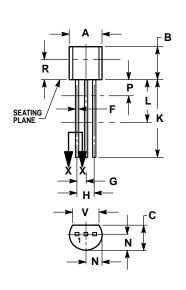
^{*} Cosp is Coss in parallel with Series Combination of Ciss and Crss.

NOTE:

 Graphical data is presented for dc conditions. Tabular data is given for pulsed conditions (Pulse Width = 630 ms, Duty Cycle = 10%).

Figure 11. Equivalent Low Frequency Circuit

PACKAGE DIMENSIONS



SECTION X-X

CASE 029-04 (TO-226AA) **ISSUE AD**

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L. DIMENSION D AND J APPLY BETWEEN L AND K
 MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIMETERS			
DIM	MIN	MAX	MIN	MAX		
Α	0.175	0.205	4.45	5.20		
В	0.170	0.210	4.32	5.33		
С	0.125	0.165	3.18	4.19		
D	0.016	0.022	0.41	0.55		
F	0.016	0.019	0.41	0.48		
G	0.045	0.055	1.15	1.39		
Н	0.095	0.105	2.42	2.66		
J	0.015	0.020	0.39	0.50		
K	0.500		12.70			
L	0.250		6.35			
N	0.080	0.105	2.04	2.66		
Р		0.100		2.54		
R	0.115		2.93			
V	0.135		3.43			

STYLE 7:

PIN 1. SOURCE

2. DRAIN

GATE

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 \Diamond 2N5460/D